

MOTOROLA  
SEMICONDUCTOR  
TECHNICAL DATA

Product Preview

System Basis Chip with  
LIN transceiver

The LIN SBC is a monolithic integrated circuit combining many functions frequently used by automotive LIN distributed slave nodes. It incorporates:

- Single voltage regulator with low power modes
- LIN physical interface.
- Wake up inputs.
- Triple high side driver
- Current sense op amp

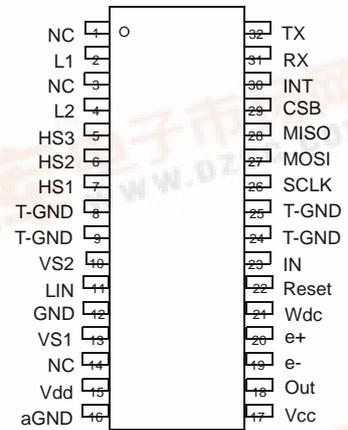
- Vdd: Low drop voltage regulator, current limitation, over temperature detection, monitoring and reset function, current capability 50mA.
- Programmable window watchdog
- Three operational modes (normal, stop and sleep modes)
- Low current consumption in sleep and stop modes
- LIN physical interface compatible with LIN standard.
- Two external high voltage wake-up inputs
- Dual high side switches, relay driver capability, internal clamp, PWM capability.
- Single low current high side switch, 50mA capability for switch bias and hall sensor supply
- Current sense amplifier
- Nominal DC operating voltage from 5.5 to 27V
- 40V maximum transient voltage
- Wake up capabilities (wake up inputs, LIN interface)

MC33689

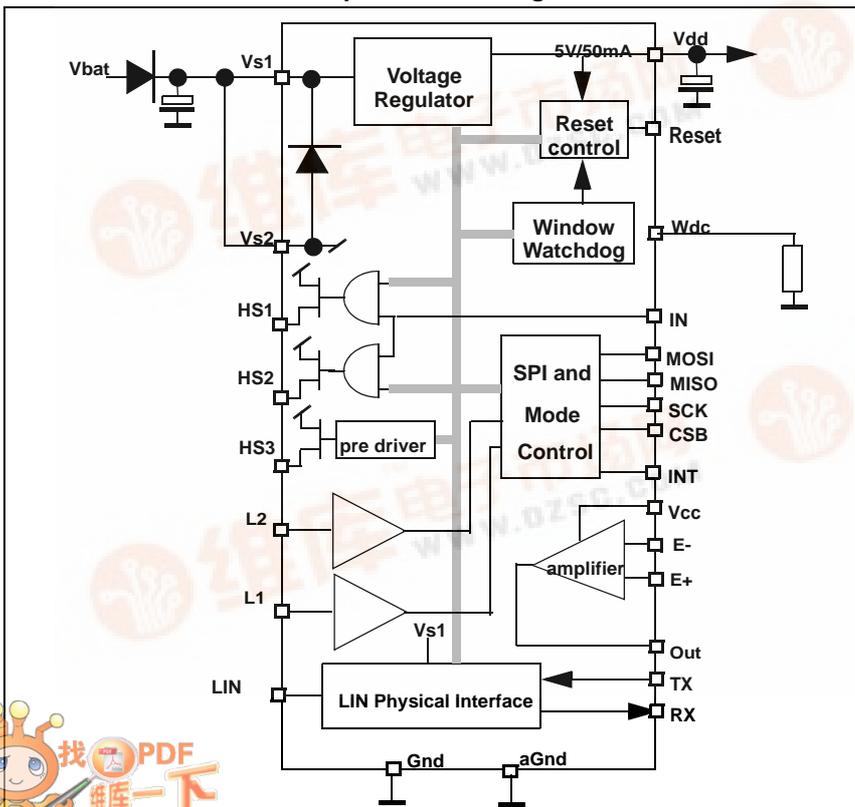
LIN System basis chip

SILICON MONOLITHIC  
INTEGRATED CIRCUIT

Pin out SO32WB fine pitch



Simplified Block Diagram



ORDERING INFORMATION

Device	Operating Temperature Range	Package
MC33689DWB/R2	T <sub>A</sub> = -40 to 125°C	SO-32

## 1 MAXIMUM RATINGS

Ratings	Symbol	Min	Typ	Max	Unit
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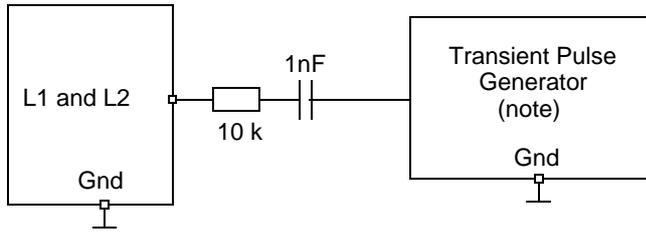
### ELECTRICAL RATINGS

Supply Voltage at Vs1 and Vs2 - Continuous voltage - Transient voltage (Load dump)	Vsupdc Vsupttr	-0.3		27 40	V
Supply Voltage Vdd and Vcc	Vdd	-0.3		5.5	V
Logic Inputs: MOSI, SCK, CSB, IN, Tx	Vinlog	- 0.3		Vdd+0.3	V
Logic output: MISO, INT, Rx, Reset	Voutlog	- 0.3		Vdd+0.3	V
Output current Vdd	Idd		Internally limited		A
E+, E- input voltage	Ve+-	-0.3		7	V
E+, E- input current	Ie+-	-20		20	mA
Out output voltage	Vout	-0.3		Vcc+0.3	V
Out output current	Iout	-20		20	mA
L1 and L2 - DC Input voltage with a 33k resistor - Transient input voltage (according to ISO7637 specification) and with external component (see figure 1 below).	Vlxdc Vlxtr	-18V -100		40 +100	V V
HS1 and HS2 output	Vhs12	internally clamped		Vs2+0.3	V
HS3	Vhs3	-0.3		Vs2+0.3	V
LIN - DC voltage Transient input voltage (according to ISO7637 specification) and with external component (see figure 1 below).	Vbusdc Vbustr	-18 -150		+40 +100	V
ESD voltage (HBM 100pF, 1.5k) (GND, T-GND and aGND pins connected together and configured as ground) - LIN, L1, L2 - All other pins	Vesdh	-4 -2		4 2	kV
ESD voltage (HBM 100pF, 1.5k) (GND pin configured as ground, T-GND and aGND pins as I/O) - LIN, L1, L2 - All other pins	Vesdh	-4 -2		4 2	kV
ESD voltage (Machine Model) All pins (GND, T-GND and aGND pins connected together and configured as ground)	Vesdm	-200		200	V
ESD voltage (Machine Model) All pins (GND pin configured as ground, T-GND and aGND pins as I/O)	Vesdm	-150		150	V

### THERMAL RATINGS

Junction Temperature	T <sub>j</sub>	- 40		+150	°C
Storage Temperature	T <sub>s</sub>	- 55		+165	°C
Ambient Temperature (for info only)	T <sub>a</sub>	- 40		+85	°C
Thermal resistance junction to ambient	Rthj/a			80	°C/W

Figure 1. : Transient test pulses for LIN and Wake pins



note: Waveform in accordance to ISO7637 part1, test pulses 1, 2, 3a and 3b.

## 2 ELECTRICAL CHARACTERISTICS

( $V_{s1}$  and  $V_{s2}$  from 5.5V to 18V and  $T_{amb}$  from -40°C to 125°C unless otherwise noted)

Description	Symbol	Characteristics			Unit	Conditions
		Min	Typ	Max		
<b>Vs1 and Vs2 pins (Device power supply)</b>						
Nominal DC Voltage range	$V_{sup}$	5.5		18	V	
Input Voltage during Load Dump	$V_{supLD}$			40	V	Load dump situation
Input Voltage during jump start	$V_{supJS}$			27	V	Jump start situation (note 1)
Supply Current in Normal Mode (note 2)	$I_{sup(norm)}$		5	7.5	mA	$I_{out}$ at $V_{dd} = 10mA$ , LIN recessive state
Supply Current in Sleep Mode (note 2)	$I_{sleep}$		30	40	uA	$V_{dd}$ off, $V_{sup} \leq 13.5V$
Supply Current in Stop Mode (note 2)	$I_{stop}$		60	75	uA	$V_{dd}$ ON with $I_{out} < 100uA$ , $V_{sup} \leq 13.5V$
Supply voltage fall early warning threshold	$VSUV_{ew}$	5.7	6	6.6	V	Normal mode, INT generated, bit VSUV set
VSUV flag hysteresis	$VSUV_{hyst}$		1		V	guaranteed by design
Supply voltage over voltage warning threshold	$VSOV_{w}$	18	19.25	20.50	V	Normal mode, INT generated, bit VSOV set
VSOV flag hysteresis	$VSOV_{hyst}$		220		mV	guaranteed by design

note 1: Device is fully functional. All functions are operating. Over temperature may occur.

note 2: Total current ( $I_{Vs1} + I_{Vs2}$ ) measured at gnd pins.

**Vdd (external 5V output for MCU supply). Specification with external capacitor  $2\mu F < C < 10\mu F$  and  $200m\Omega \leq ESR \leq 10\Omega$ . Normal mode. Capacitor value up to 47uF chemical can be used.**

Vdd Output Voltage	$V_{ddout}$	4.75	5	5.25	V	$I_{dd}$ from 2 to 50mA $5.5V < V_{sup} < 27V$
Dropout Voltage (note 1)	$V_{dddrop}$		100	200	mV	$I_{dd} = 50mA$ (note 1) $V_{sup} > 4.5V$
$I_{dd}$ output current limitation (note 2)	$I_{dd}$	50	110	200	mA	Internally limited
Over temperature pre warning (junction)	$T_{pre}$	120	135	160	°C	Normal mode, INT generated, Bit $V_{ddT}$ set guaranteed by design
Thermal Shutdown (junction)	$T_{sd}$	155	170		°C	Normal mode guaranteed by design
Temperature threshold difference		20	30	45	°C	Normal mode ( $T_{sd} - T_{pre}$ ) guaranteed by design
$V_{sup}$ range for Reset Active	$V_{sup_r}$	3.5			V	$0.5 < V_{dd} < V_{dd}$ ( $R_{st-th1}$ )
Line Regulation	LR		20	150	mV	$5.5V < V_{sup} < 27V$ , $I_{dd} = 10mA$
Load Regulation	LD		40	150	mV	$1mA < I_{dd} < 50mA$

note 1: measured when voltage has dropped 100mV below its nominal value.

note 2: total Vdd regulator current. A 5mA current for operational amplifier operation is included. Digital output supplied from Vdd.

**Vdd: in Stop mode**

Vdd Output Voltage (note 1)	$V_{ddstop}$	4.75	5.00	5.25	V	$I_{dd} \leq 2mA$
$I_{dd}$ current capability (note 2)	$I_{dds}$	4	8	14	mA	Stop mode
Line regulation	LR-s		10	100	mV	$5.5V < V_{sup} < 27V$ , $I_{dd} = 2mA$
Load regulation	LD-s		40	150	mV	$1mA < I_{dd} < 5mA$

note 1: when switching from Normal mode to Stop mode, or from Stop mode to Normal mode the output voltage can varies within the output voltage specification.

note 2: when  $I_{dd}$  is above  $I_{dds}$  device enters reset mode

**Reset: normal and stop modes (output pin only)**

Reset threshold	$R_{st-th1}$	4.50	4.68	$V_{dd} - 0.2$	V	
High Level Output current	$I_{oh}$		-250		uA	$V_{out} > 0.7V_{dd}$
Low Level Output Voltage ( $I_o = 1.5mA$ )	$V_{ol}$	0		0.9	V	$4.5V < V_{sup} < 27V$

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( $V_{s1}$  and  $V_{s2}$  from 5.5V to 18V and  $T_{amb}$  from -40°C to 125°C unless otherwise noted)

Description	Symbol	Characteristics			Unit	Conditions
		Min	Typ	Max		
Reset pull down current	lpdw	1.5		8	mA	Internally limited. $V_{dd} < 4V$ , $V_{reset} = 4.6V$
Reset Duration after Vdd High	reset-dur	0.65	1	1.35	ms	

## IN: input

High Level Input Voltage	Vih	0.7Vdd		Vdd+0.3	V	
Low Level Input Voltage	Vil	-0.3		0.3Vdd	V	
Input Current	Iin	-10		10	μA	$0 < V_{IN} < V_{dd}$

## MISO: SPI output

Low Level Output Voltage	Vol	0		1.0	V	I out = 1.5mA
High Level Output Voltage	Voh	Vdd-0.9		Vdd	V	I out = -250uA
Tristated MISO Leakage Current		-2		+2	uA	$0V < V_{miso} < V_{dd}$

## MOSI, SCLK, CSB: SPI input

High Level Input Voltage	Vih	0.7Vdd		Vdd+0.3		
Low Level Input Voltage	Vil	-0.3		0.3Vdd	V	
CSB Pull up current source	Iih	-100		-20	uA	$V_i$ 1V to 3.5V
MOSI, SCK Input Current	Iin	-10		10	uA	$0 < V_{IN} < V_{dd}$

## SPI: DIGITAL INTERFACE TIMING

SPI operation frequency	Freq	0.25		4	MHz	
SCLK Clock Period	$t_{pCLK}$	250		N/A	ns	
SCLK Clock High Time	$t_{wSCLKH}$	125		N/A	ns	
SCLK Clock Low Time	$t_{wSCLKL}$	125		N/A	ns	
Falling Edge of CS to Rising Edge of SCLK	$t_{lead}$	100		N/A	ns	
Falling Edge of SCLK to CS Rising Edge	$t_{lag}$	100		N/A	ns	
MOSI to Falling Edge of SCLK	$t_{SISU}$	40		N/A	ns	
Falling Edge of SCLK to MOSI	$t_{SIH}$	40		N/A	ns	
MISO Rise Time (CL = 220pF)	$t_{rSO}$		25	50	ns	guaranteed by design
MISO Fall Time (CL = 220pF)	$t_{fSO}$		25	50	ns	guaranteed by design
Time from Falling or Rising Edges of CS to: - MISO Low Impedance - MISO High Impedance	$t_{SOEN}$ $t_{SODIS}$	0		50 50	ns	guaranteed by design
Time from Rising Edge of SCLK to MISO Data Valid	$t_{valid}$	0		50	ns	$0.2 V_1 = <MISO> = 0.8 V_1$ , $C_L = 100pF$ guaranteed by design

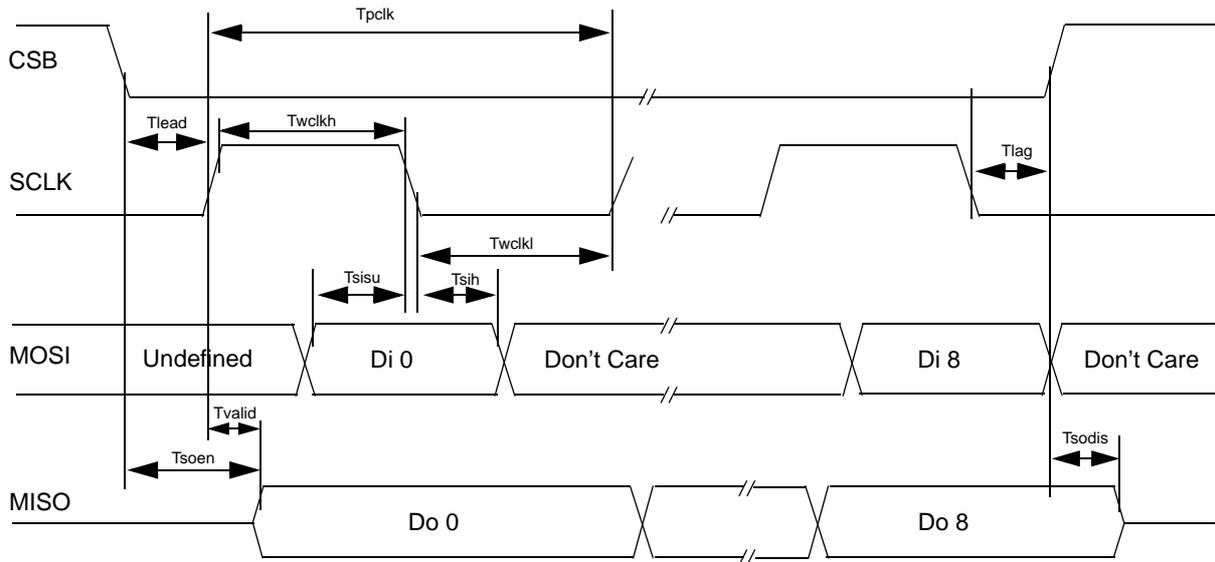
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( $V_{s1}$  and  $V_{s2}$  from 5.5V to 18V and  $T_{amb}$  from -40°C to 125°C unless otherwise noted)

Description	Symbol	Characteristics			Unit	Conditions
		Min	Typ	Max		

Figure 2. SPI Timing characteristic



**Note:**

Incoming data at MOSI pin is sampled by the SBC at SCLK falling edge.  
Outcoming data at MISO pin is set by the SBC at SCLK rising edge (after Tvalid delay time)

**INT: output pin**

Low Level Output Voltage ( $I_o=1.5mA$ )	$V_{ol}$	0		0.9	V	
High Level Output Voltage ( $I_o=-250uA$ )	$V_{oh}$	$V_{dd}-0.9$		$V_{dd}$		

**WDC: window watchdog configuration pin**

External resistor range	$R_{ext}$	10		100	kohms	
Watchdog period accuracy with external resistor	$W_{dacc}$	-15		15	%	Excluding resistor accuracy. Note 1
Watchdog period with external resistor	$W_{dp 10}$		10.558		ms	$R = 10$ kohms. note 1
Watchdog period with external resistor	$W_{dp 100}$		99.748		ms	$R = 100$ kohms. note 1
Watchdog period without external resistor, Conf pin open	$PW_{doff}$	97	150	205	ms	Normal mode

**note 1:** watchdog timing period calculation formula:  $T_{wd} = 0.991 * R + 0.648$  (R in kohms and  $T_{wd}$  in ms).

**HS1 and HS2: High side output pin**

$R_{dson}$ at $T_a=25^\circ C$ , and $I_{out} -150mA$	$R_{on25}$		2	2.5	Ohms	$V_{sup}>9V$
$R_{dson}$ at $T_a=125^\circ C$ , and $I_{out} -150mA$	$R_{on125}$			4.5	Ohms	$V_{sup}>9V$
$R_{dson}$ at $T_a=125^\circ C$ , and $I_{out} -120mA$	$R_{on3}$		3		Ohms	$5.5<V_{sup}<9V$
Output current limitation	$I_{lim}$	300	430	600	mA	
Over temperature Shutdown	$O_{vt}$	155		190	$^\circ C$	note 1
Leakage current	$I_{leak}$			10	$\mu A$	
Output Clamp Voltage at $I_{out} = -100mA$	$V_{cl}$	-6			V	

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( $V_{s1}$  and  $V_{s2}$  from 5.5V to 18V and  $T_{amb}$  from -40°C to 125°C unless otherwise noted)

Description	Symbol	Characteristics			Unit	Conditions
		Min	Typ	Max		

note 1: when over temperature occurs, switch is turned off and latched off. Flag is set in SPI.

### HS3: High side output pin

Rdson at $T_j=25^\circ\text{C}$ , and $I_{out} -50\text{mA}$	Ron25			7	Ohms	$V_{sup}>9\text{V}$
Rdson at $T_a=125^\circ\text{C}$ , and $I_{out} -50\text{mA}$	Ron125			10	Ohms	$V_{sup}>9\text{V}$
Rdson at $T_a=125^\circ\text{C}$ , and $I_{out} -30\text{mA}$	Ron3			14	Ohms	$5.5<V_{sup}<9\text{V}$
Output current limitation	Ilim	60	100	200	mA	
Over temperature Shutdown	Ovt	155		190	°C	note 1
Leakage current	Ileak			10	uA	

note 1: when over temperature occurs, switch is turned off and latched off. Flag is set in SPI

### SENSE CURRENT AMPLIFIER SECTION:

Rail to rail input voltage	$V_{imc}$	-0.1		$V_{cc}+0.1$	V	
Output voltage range	$V_{out1}$	0.1		$V_{cc}-0.1$	V	Output current +- 1mA
Output voltage range	$V_{out2}$	0.3		$V_{cc}-0.3$	V	Output current +- 5mA
Input bias current	$I_b$			250	nA	
Input offset current	$I_o$	-100		100	nA	
Input offset voltage	$V_{io}$	-15		15	mV	
Supply voltage rejection ratio	SVR	60			dB	Guaranteed by design
Common mode rejection ratio	CMR	70			dB	Guaranteed by design
Gain bandwidth	GBP	1			MHz	Guaranteed by design
Slew rate	SR	0.5			V/us	
Phase margin	PHMO	40			°	For gain=1, load 100pF//5kohms. Guaranteed by design
Open loop gain	OLG		85		dB	Guaranteed by design

### L1, L2 inputs

Negative Switching Threshold	$V_{thn}$	2 2.5 2.7	2.5 3 3.2	3 3.5 3.7	V	$5.5\text{V}<V_{sup}<6\text{V}$ $6\text{V}<V_{sup}<18\text{V}$ $18\text{V}<V_{sup}<27$
Positive Switching Threshold	$V_{thp}$	2.7 3 3.5	3.3 4 4.2	3.8 4.5 4.7	V	$5.5\text{V}<V_{sup}<6\text{V}$ $6\text{V}<V_{sup}<18\text{V}$ $18\text{V}<V_{sup}<27$
Hysteresis	$V_{hyst}$	0.5		1.3	V	$5.5\text{V}<V_{sup}<27$
Input current	$I_{in}$	-10		10	uA	$-0.2\text{V} < V_{in} < 40\text{V}$
Wake up Filter Time	$T_{wuf}$	8	20	38	us	Guaranteed by design

### STATE MACHINE TIMING

Delay between CSB low to high transition (at end of SPI stop command) and Stop mode activation (Guaranteed by design)	$T_{stop-m}$	1.4		5	us	Minimum Watchdog period No watchdog selected Maximum watchdog period
	$T_{stop-nw}$	6		30	us	
	$T_{stop-M}$	12		50	us	
Interrupt low level duration	$T_{int}$	7	10	13	us	
Internal oscillator frequency accuracy	Osc-f1	-35		35	%	All modes, for info only
Normal request mode time out	NRtout	97	150	205	ms	Normal request mode
Delay between SPI command and HS1, HS2 or HS3 turn on (note 1, 2)	$T_s\text{-HSon}$			20	us	Normal mode $V_{sup}>9\text{V}$ , $V_{hs} \geq 0.2 V_{s1}$
Delay between SPI command and HS1, HS2 or HS3 turn off (note 1, 2)	$T_s\text{-HSoff}$			20	us	Normal mode $V_{sup}>9\text{V}$ , $V_{hs} \leq 0.8 V_{s1}$
Delay between Normal Request and Normal mode, after W/D trigger command	$T_s\text{-NR2N}$	6	35	30	us	Normal request mode, Guaranteed by design
Delay between CSB wake up (CSB low to high) and SBC normal request mode ( $V_{dd1}$ on & reset high)	$T_w\text{-csb}$	15	40	80	us	SBC in stop mode

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(V<sub>s1</sub> and V<sub>s2</sub> from 5.5V to 18V and T<sub>amb</sub> from -40°C to 125°C unless otherwise noted)

Description	Symbol	Characteristics			Unit	Conditions
		Min	Typ	Max		
Delay between CSB wake up (CSB low to high) and first accepted SPI command	Tw-spi	90		N/A	us	SBC in stop mode
Delay between INT pulse and 1st SPI command accepted	Ts-1stspi	30		N/A	us	In stop mode after wake up
The minimum time between two rising edges on the CSB	T2csb	15			us	

note 1: when IN input is set to high, delay starts at falling edge of clock cycle #8 of the SPI command and start of device activation/deactivation. 30mA load on HS switches. Excluding rise or fall time due to external load.

note 2: when IN used to control HS switches, delays measured between IN and HS1 or HS2 on /off. 30mA load on HS switches. Excluding rise or fall time due to external load.

## Rx: LIN physical layer output

Low Level Voltage Output	V <sub>ol</sub>	0		0.9	V	I <sub>in</sub> ≤ +1.5mA
High Level Voltage Output	V <sub>oh</sub>	3.75		5.25	V	I <sub>out</sub> ≤ 250uA

## Tx: LIN physical layer input

Low Level Voltage Input	V <sub>il</sub>			1.5	V	
High Level Voltage Input	V <sub>ih</sub>	3.5			V	
Input Threshold Hysteresis	V <sub>inhyst</sub>	50	550	800	mV	
Pull-up Current Source	I <sub>s</sub>	-100		-20	uA	1V < V(Tx) < 3.5V

## LIN: physical layer bus (Voltage Expressed versus V<sub>sup</sub> Voltage)

Low Level Dominant Voltage	V <sub>lin-low</sub>			1.4	V	external bus pull 500 Ohms
High Level Voltage (Tx high, I <sub>out</sub> = 1uA)	V <sub>lin-high</sub>	V <sub>sup</sub> -1			V	Recessive state
Pull up Resistor to V <sub>sup</sub>	R <sub>pu</sub>	20	30	47	kohms	In normal mode. In sleep and stop mode if not turned off by SPI
Pull up current source	I <sub>pu</sub>		1.3		uA	In sleep and stop mode with 30k disconnected
Over current shutdown threshold	I <sub>ov-cur</sub>	50	75	150	mA	
Over current shutdown delay	I <sub>ov-delay</sub>		10		us	Guaranteed by design
Leakage Current to GND	I <sub>bus-pas-rec</sub>	0	3	20	uA	Recessive state, V <sub>sup</sub> 8V to 18V, V <sub>lin</sub> 8V to 18V
Gnd disconnected, V <sub>gnd</sub> = V <sub>sup</sub> , V <sub>Lin</sub> at -18V	I <sub>bus no gnd</sub>	-1		1	mA	
Leakage Current to GND, V <sub>sup</sub> Disconnected, V <sub>Lin</sub> at +18V	I <sub>bus</sub>		1	10	uA	V <sub>sup</sub> disconnected V <sub>lin</sub> at +18V
Lin Receiver V <sub>il</sub> (Tx high, Rx low)	V <sub>lin-vil</sub>	0		0.4V <sub>SUP</sub>		
Lin Receiver V <sub>ih</sub> (Tx high, Rx high)	V <sub>lin-vih</sub>	0.6 V <sub>SUP</sub>		V <sub>SUP</sub>		
LIN Receiver Threshold center	V <sub>lin-thres</sub>	0.475	0.5	0.525	V <sub>sup</sub>	(V <sub>lin-vih</sub> - V <sub>lin-vil</sub> ) / 2
LIN Receiver Input Hysteresis	V <sub>lin-hyst</sub>			0.175	V <sub>sup</sub>	V <sub>lin-vih</sub> - V <sub>lin-vil</sub>
LIN wake up threshold	V <sub>lin-wu</sub>		0.5		V <sub>sup</sub>	

## LIN physical layer: bus driver timing characteristics for normal slew rate (note 1)

Dominant propagation delay Tx to LIN	t <sub>dom min</sub>			50	us	Measurement threshold 58.1% V <sub>sup</sub>
Dominant propagation delay Tx to LIN	t <sub>dom max</sub>			50	us	Measurement threshold 28.4% V <sub>sup</sub>
Recessive propagation delay Tx to LIN	t <sub>rec min</sub>			50	us	Measurement threshold 42.2% V <sub>sup</sub>
Recessive propagation delay Tx to LIN	t <sub>rec max</sub>			50	us	Measurement threshold 74.4% V <sub>sup</sub>
Prop delay symmetry: t <sub>dom min</sub> - t <sub>rec max</sub>	dt1	-10.44		-	us	

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Prop delay symmetry: tdom max - trec min	dt2	-		11	us	
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note 1: Vsup from 7V to 18V, bus load R0 and C0 1nF/1k, 6.8nF/660, 10nF/500. Measurement thresholds: 50% of Tx signal to LIN signal threshold defined in the column "condition"

## LIN physical layer: bus driver timing characteristics for slow slew rate (note 1)

Dominant propagation delay Tx to LIN	tdom min			100	us	Measurement threshold 61.6% Vsup
Dominant propagation delay Tx to LIN	tdom max			100	us	Measurement threshold 25.1% Vsup
Recessive propagation delay Tx to LIN	trec min			100	us	Measurement threshold 38.9% Vsup
Recessive propagation delay Tx to LIN	trec max			100	us	Measurement threshold 77.8% Vsup
Prop delay symmetry: tdom min - trec max	dt1s	-22		-	us	
Prop delay symmetry: tdom max - trec min	dt2s	-		23	us	

note 1: Vsup from 7V to 18V, bus load R0 and C0 1nF/1k, 6.8nF/660, 10nF/500. Measurement thresholds: 50% of Tx signal to LIN signal threshold defined in the column "condition"

## LIN physical layer: bus driver fast slew rate

LIN high slew rate (programming mode)	Dv/Dt fast			13	V/us	Fast slew rate
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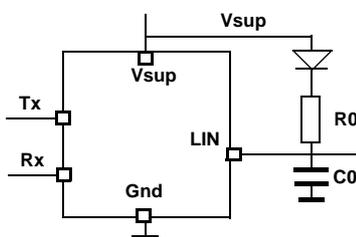
## LIN physical layer: receiver characteristics and wake up timings

Receiver dominant propagation delay	TrL		3.5	6	us	LIN low to Rx low. Note 2
Receiver recessive propagation delay	TrH		3.5	6	us	LIN high to Rx high. note 2
Receiver prop delay symmetry	Tr-sym	-2		2	us	TrL - TrH
Bus wake up deglitcher	TpropWL	30	70	90	us	Sleep and stop mode
Bus wake up event reported	Twake		20		us	Note 3

note 2: Measured between LIN signal threshold "Lin-vil" or "Lin-vih" and 50% of Rx signal.

note 3: Twake is typically 2 internal clock cycles after LIN rising edge detected. Ref to "LIN bus wake up behavior" figure. In sleep mode the Vdd rise time is strongly dependant upon the decoupling capacitor at Vdd pin.

Figure 3. Test circuit for timing measurements



R0 and C0: 1k/1nF, 660ohms/6.8nF and 500ohms/10nF

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Figure 4. timing measurements for normal slew rate

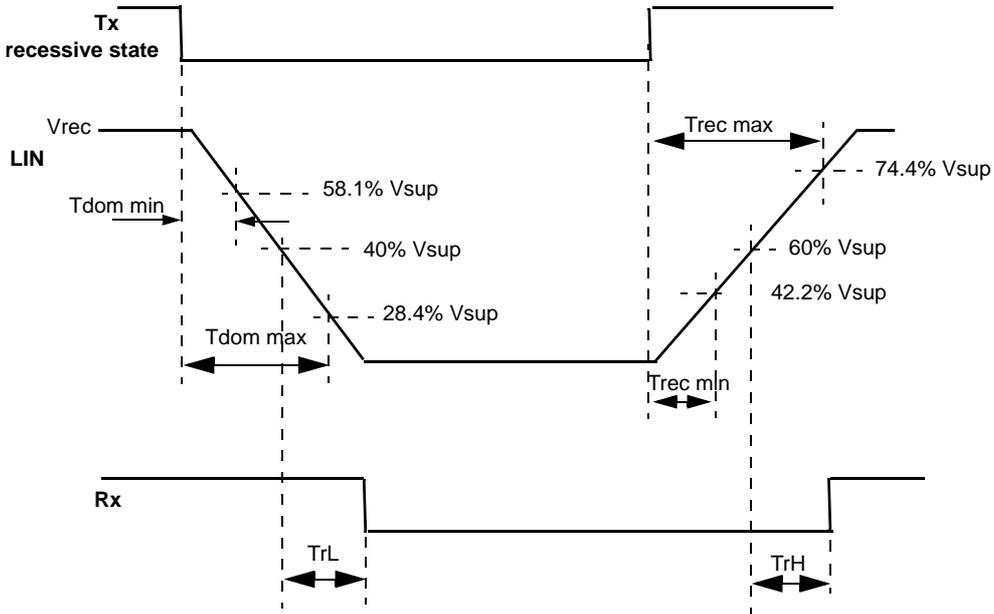


Figure 5. timing measurements for slow slew rate

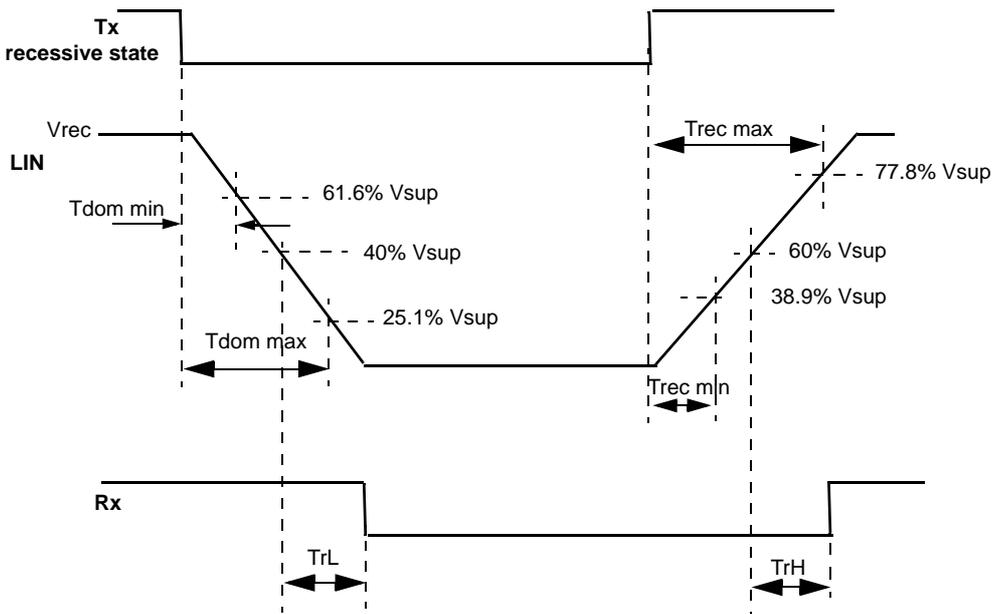
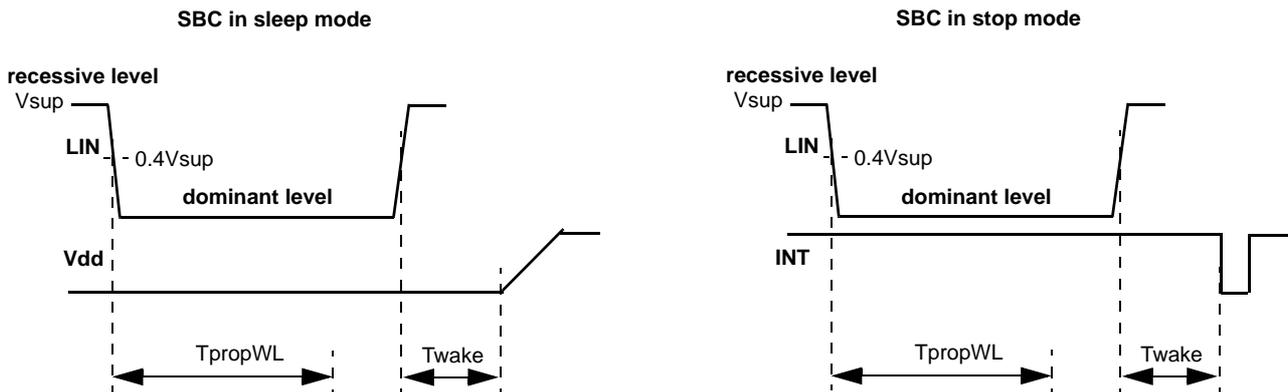
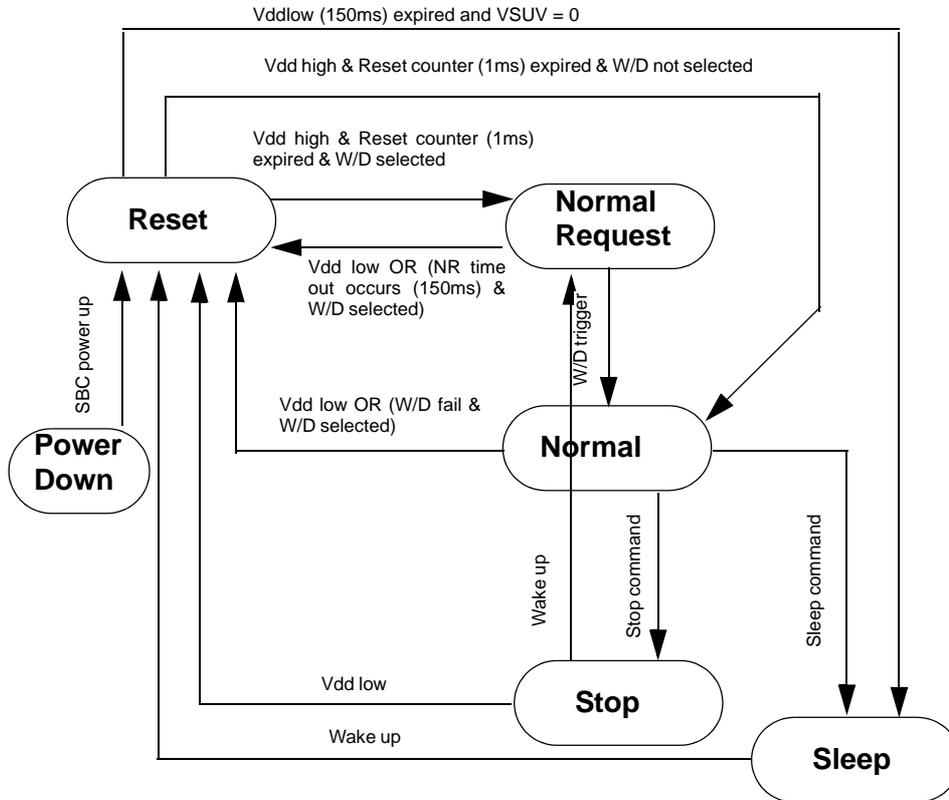


Figure 6. LIN bus wake up behavior



3 STATE MACHINE



W/D selected means: external resistor between Wdc pin and gnd or Wdc pin open.  
 W/D not selected means Wdc pin connected to gnd.  
 W/D fail means: W/D trigger occurs in closed window or no SPI W/D trigger command.  
 Stop command means: SPI stop command.  
 Sleep command means: SPI sleep request followed by SPI sleep command.  
 Wake up means: L1 or L2 state change or LIN bus wake up or CSB rising edge.

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## 4 PIN DESCRIPTION

pin name	Pin number	function
Vs1	13	Power supply pin. Supply for the voltage regulator and the internal logic.
Vs2	10	Power supply pin. Supply for the high side switches.
GND	12	Electrical ground pin pins for the device.
aGND	16	Analog ground pin for voltage regulator and sense amplifier.
T-GND	8,9,24,25	Thermal ground pins for the device
Vdd	15	5V regulator output.
Reset	22	Reset output
Wdc	21	Configuration pin for the watchdog. A resistor is connected to this pin. The resistor value defines the watchdog period. If the pin is open, the W/D period is fixed (default value). If this pin is tied to gnd the watchdog is disabled.
Tx	32	Transmitter input of the LIN interface
Rx	31	Receiver output of the LIN interface
LIN	11	LIN bus line
HS1, HS2, HS3	7,6,5	High side driver output 1, output 2 and output 3
L1, L2	2,4	Wake input 1, wake up input 2
Vcc	17	5V supply input of operational amplifier
E-	19	Inverted input of the sense amplifier
E+	20	Non inverted input of the sense amplifier
Out	18	Output of the sense amplifier
MOSI	27	SPI: Master Out Slave In pin
MISO	28	SPI: Master In Slave Out
SCLK	26	SPI: Clock input pin
CSB	29	SPI: Device chip select pin
INT	30	Interrupt output pin AND wake up event signalling in stop mode.
IN	23	Direct input for PWM control of High Side switches 1 and 2

Table 4-1.

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## 5 GENERAL DESCRIPTION

The LIN SBC is an integrated circuit dedicated to automotive applications. It includes the following functions:

- One full protected voltage regulator with 50mA total output current capability available at Vdd external pin, with under voltage reset function.
- Programmable window watchdog function, INT output
- Wake up from Lx wake input and LIN bus
- LIN physical interface
- Two 150mA high side protected switches PWM capable for relay or lamp drive
- One 50mA high side protected switch for hall sensor or
- Current sense op amp

### 5.1 Device Supply

The device is supplied from the battery line through the Vs1 and VS2 pins. An external diode is required to protect against negative transients and reverse battery. It can operate from 4.5V and under the jump start condition at 27V DC. Device functionality is guaranteed down to 4.5V at VS1 and VS2 pins. This pin sustains standard automotive voltage conditions such as load dump at 40V.

### 5.2 Over and under voltage warning.

If the voltage at VS1 exceed 20V typical or falls below 6V typical, the device generates an INT. VSOV or VSUV bits are set in the SPI register. Information is latched until the bit is read AND the fault has disappeared. The interrupt is not maskable.

### 5.3 LIN physical interface:

The device contains an integrated LIN physical interface.

### 5.4 L1 and L2 inputs:

These pins are used to sense external switches and to wake up the device from sleep or stop mode. During normal mode the state of these pins can be read through SPI.

### 5.5 HS1 and HS2:

These are two high side switches to drive load such as relays or lamps. They are protected against over current and over temperature and include internal clamp circuitry for inductive load drive. Control is done through SPI. PWM capability is offered through the IN input.

If PWM control is required, the internal circuitry which drive the internal high side switch is an AND function between the SPI bit HS1 (or HS2) and the IN input. In order to have HS1 on, bit HS1 must be set and IN input must be tied to a micro controller PWM output to generate the PWM control signal (HS1 on when IN is high, HS1 off when IN is low). Same for HS2 output.

If not PWM control is required, IN input must be connected to Vdd or to a high logic level, then the control of HS1 and HS2 is done through SPI only.

If over temperature occurs on any of the 3 switches, the faulty switch is turned off and latched off until HS1 (or HS2 or HS3) bit is set to 1 in the SPI register. The failure is reported through SPI by HSSt bit.

### 5.6 HS3:

This high side switch can be used to drive small lamps, hall sensor or switch pull up resistors. Control is done through SPI

### 5.7 Sense amplifier:

E+, E- and OUT are the 3 terminations of the current sense amplifier. The amplifier is enable in normal mode only.

### 5.8 Mode of operation

Mode are controlled by the mode1 and mode 2 bits in the SPI register. 3 modes are available: sleep, stop and normal.

The operation modes and the associated functions are described in the table below.

Device Mode	Voltage Regulator	Wake up capabilities	Reset output	Watchdog function	HS1 HS2 HS3	LIN interface	Operational amplifier
Reset	Vdd: ON	N/A	Low for typ 1ms, then high (if Vdd above threshold)	Disable	OFF	Recessive only	Not active
Normal Request	Vdd: ON	N/A	- High. - Active low if Vdd under voltage occurs and if Normal Request timeout (if W/D enable)	150ms time out if W/D enabled.	ON or OFF	Transmit and Receive	Not active

Table 5-1.

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Device Mode	Voltage Regulator	Wake up capabilities	Reset output	Watchdog function	HS1 HS2 HS3	LIN interface	Operational amplifier
Normal	Vdd: ON	N/A	- High. - Active low if Vdd under voltage occurs or if W/D fail (if W/D enable)	Window WD if enabled.	ON or OFF	Transmit and Receive	Active
Stop	Vdd ON, limited current capability	LIN and state change on Lx inputs	- Normally high. - Active low if Vdd under voltage occurs	Disable	OFF	Recessive state with Wake capability	Not active
Sleep	Vdd OFF, (Set to 5V after wake up to enter Normal request)	LIN and state change on Lx inputs	- Low - Go to high after wake up and Vdd within spec	Disable	OFF	Recessive state with Wake capability	Not active

Table 5-1.

### Sleep and stop mode enter:

To safely enter sleep or stop mode and to ensure that these modes are not entered by noise issue during SPI transmission, a dedicated sequence combining bit controlling the LIN bus and the device mode must be send twice.

Enter sleep mode: first and second SPI commands (with bit D6=1, D7=1, D5 =0 or 1, D1=0 and D0=0) 11x0\_0000 must be sent.

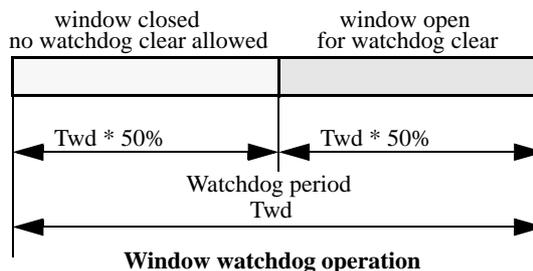
Enter stop mode: first and second SPI commands (with bit D6=1, D7=1, D5 =0 or 1, D1=0 and D0=1) 11x0\_0001 must be sent.

Sleep or stop mode is entered after the second SPI command. D5 bit must be set accordingly.

### 5.9 Window watchdog.

The window watchdog is configurable using external resistor at Wdc pin. The W/D is cleared through mode1 and mode 2 bit is SPI register. If Wdc pin is left open a fixed watchdog period is selected (typ 150ms). If no watchdog function is required or to disable the watchdog, the Wdc pin must be connected to gnd. The watchdog period is calculated by the following formula:

$$T_{wd} = 0.991 * R + 0.648 \text{ (with R in kohms and } T_{wd} \text{ in ms)}$$



Watchdog clear:

The watchdog is cleared by SPI write command with following mode1 and mode2 bits.

Mode 2	Mode 1	Mode
0	0	Sleep mode (note 1)
0	1	Stop mode
1	0	Normal mode + W/D clear (note 2)
1	1	Normal mode

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Note 1: Special SPI command and sequence is implemented in order to avoid to go into sleep or stop mode with a single 8 bit SPI command.

Note 2: When a zero is written to "Mode1" bit while "Mode2" bit is written as a one, after the SPI command is completed "Mode1" bit is set to one and SBC stays in normal mode. In order to set the SBC in sleep mode, both "Mode1" and "Mode2" bits must be written in the same 8 bits SPI command.

The W/D clear on normal request mode (150ms) has no window.

### 5.10 INT pin:

This pin is used to report fault to the MCU. Int pulse is generated in case of:

- Vdd regulator temperature pre warning
- high side switch 1, 2 or 3 thermal shutdown
- Vsup over voltage (20V typ)
- Vsup under voltage (6V typ).

If an INT is generated, when the next SPI read operation is performed bit D7 is set to 1. This mean that the bits (D6 to D0) report the interrupt source.

In case of wake up from stop mode, INT is set low in order to signal to the MCU wake up event from L1, L2 or LIN bus.

## 6 SPI INTERFACE AND REGISTER DESCRIPTION

### 6.1 Data format description



The SPI is an 8 bits SPI. All bits are data bytes. The MSB is send first. The minimum time between two rising edges on the CSB pin is 15us.

During an SPI communication the state of MISO reports the state of the SBC, at time of CSB high to low transitions. The status flag are latched at CSB high to low transitions.

Following tables describe the SPI register bit meaning, "reset value" and "bit reset condition".

		D7	D6	D5	D4	D3	D2	D1	D0
	W	LINSL2	LINSL1	LIN-PU	HS3	HS2	HS1	Mode2	Mode1
	R	INT source	LINWU or LINFAIL	VSOV	VSUV BATFAIL (note1)	VddT	HSst	L2	L1
Write Reset value		0	0	0	0	0	0	-	-
Write Reset condition		POR, RESET	POR, RESET	POR	POR, RESET	POR, RESET	POR, RESET		

Note 1: The first SPI read, after reset, returns the BATFAIL flag state on bit D4.

D7 signals INT source. After INT occur, D7 read as a "1" means other bits report the INT source. D7 read as a "0" mean no INT occurred and other bit report real time status.

### 6.2 Write control bits:

#### 6.2.1 Mode control bits:

Mode 2	Mode 1	Description
0	0	Sleep mode
0	1	Stop mode
1	0	Normal mode + W/D clear
1	1	Normal mode

#### 6.2.2 High side switches control bits:

HS1	Description	HS2	Description	HS3	Description
0	HS1 off	0	HS2 off	0	HS3 off
1	HS1 on (if IN = 1)	1	HS2 on (if IN = 1)	1	HS3 on

#### 6.2.3 LIN pull up termination control bits:

LIN-PU	Description
0	30k pull up connected in sleep and stop mode
1	30k pull up disconnected in sleep and stop mode

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## 6.2.4 LIN slew rate control and device low power mode pre selection:

LINSL2	LINSL1	Description
0	0	Lin slew rate normal (baud rate up to 20kb/s)
0	1	Lin slew rate slow (baud rate up to 10kb/s)
1	0	Lin slew rate fast (for program download, baud rate up to 100kb/s)
1	1	Low power mode (sleep or stop mode) request, no change in LIN slew rate

## 6.3 Read control bits:

### 6.3.1 Switch input wake up and real time status:

L2	Description	L1	Description
0	L2 input low	0	L1 input low
1	L2 input high or wake up by L2 (first register read after wake up)	1	L1 input high or wake up by L1 (first register read after wake up)

### 6.3.2 High side switch, voltage regulator and device supply status

HSst	Description	VddT	Description	VSUV BATFAIL	Description	VSOV	Description
0	HS no over temp	0	No over temperature	0	Vsup above 6V	0	Vsup below 19V
1	HS1,2 or 3 OFF (over temp)	1	Vdd over temperature pre warning	1	Vsup below 6V	1	Vsup above 18V

### 6.3.3 LIN bus status

LINWU LINFALL	Description
0	No LIN bus wake up of failure
1	LIN bus wake up occurred or LIN over current or over temperature

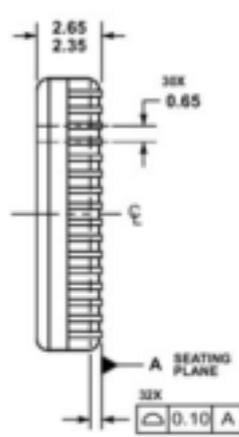
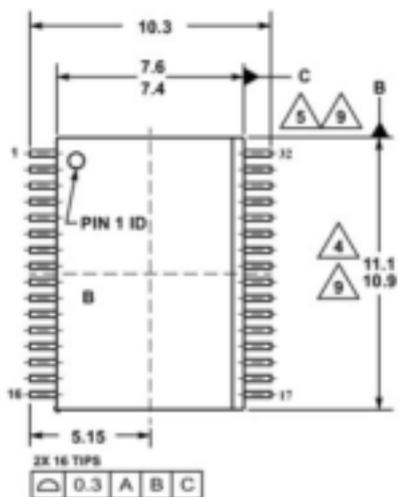
### 6.3.4 Interrupt status

INT mask	Description
0	SPI word read reflects the flag state
1	SPI word read reflects the interrupt or wake up source

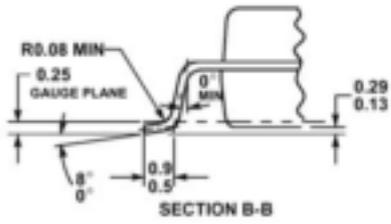
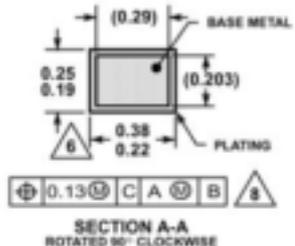
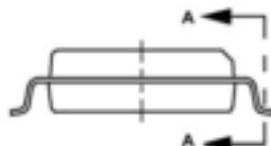
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MC33689

## DWB SUFFIX (32-LEAD SOIC) PLASTIC PACKAGE CASE 1324 ISSUE A



- NOTES:
1. ALL DIMENSIONS ARE IN MILLIMETERS.
  2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  3. DATUMS B AND C TO BE DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- △ THIS DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
  - △ THIS DIMENSION DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS. INTERLEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
  - △ THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.4 MM PER SIDE. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 MM.
  - △ EXACT SHAPE OF EACH CORNER IS OPTIONAL. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10 MM AND 0.3 MM FROM THE LEAD TIP.
  - △ THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM. THIS DIMENSION IS DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, GATE BURRS, GATE BURRS AND INTER-LEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.



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